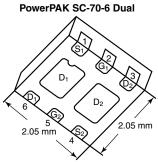
HALOGEN FREE





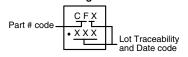
Dual N-Channel 12 V (D-S) MOSFET

PRODUCT SUMMARY									
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A) ^a	Q _g (Typ.)						
12	$0.028 \text{ at V}_{GS} = 4.5 \text{ V}$	4.5							
	0.033 at V _{GS} = 2.5 V	4.5	6.2 nC						
	0.042 at Vgs = 1.8 V	4.5							



Ordering Information: SiA910EDJ-T1-GE3 (Lead (Pb)-free and Halogen-free)

Marking Code

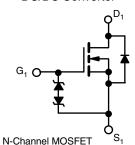


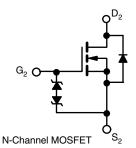
FEATURES

- TrenchFET® Power MOSFET
- Thermally Enhanced PowerPAK® SC-70 Package
 - Small Footprint Area
 - Low On-Resistance
- Typical ESD Protection: 2400 V
- 100 % R_a Tested
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

- Load Switch for Portable Applications
- High Frequency DC/DC Converter
- DC/DC Converter





Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	12	V	
Gate-Source Voltage		V _{GS}	± 8		
Continuous Drain Current (T _J = 150 °C)	$T_{C} = 25 ^{\circ}\text{C}$ $T_{C} = 70 ^{\circ}\text{C}$ $T_{A} = 25 ^{\circ}\text{C}$ $T_{A} = 70 ^{\circ}\text{C}$	I _D	4.5 ^a 4.5 ^a 4.5 ^{a, b, c} 4.5 ^{a, b, c}	A	
Pulsed Drain Current		I _{DM}	20		
Continuous Source-Drain Diode Current	$T_C = 25 ^{\circ}C$ $T_A = 25 ^{\circ}C$	I _S	4.5 ^a 1.6 ^{b, c}	_	
Maximum Power Dissipation	$T_{C} = 25 ^{\circ}\text{C}$ $T_{C} = 70 ^{\circ}\text{C}$ $T_{A} = 25 ^{\circ}\text{C}$ $T_{A} = 70 ^{\circ}\text{C}$	P _D	7.8 5 1.9 ^{b, c} 1.2 ^{b, c}	W	
Operating Junction and Storage Temperatur	e Range	T _J , T _{stg}	- 55 to 150	°C	
Soldering Recommendations (Peak Temper	ature) ^{d, e}		260		

THERMAL RESISTANCE RATINGS									
Parameter		Symbol	Typical	Maximum	Unit				
Maximum Junction-to-Ambient ^{b, f}	t ≤ 5 s	R _{thJA}	52	65	°C/W				
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	12.5	16]				

Notes:

- a. Package limited
- b. Surface mounted on 1" x 1" FR4 board.
- d. See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under steady state conditions is 110 °C/W.

Document Number: 65535 S13-0460-Rev. B, 04-Mar-13 For technical questions, contact: pmostechsupport@vishav.com



SPECIFICATIONS ($T_J = 25 ^{\circ}C$, Parameter		Test Conditions	Min.	Tyro	Max	Unit		
Static	Symbol	rest Conditions	IVIII1.	Тур.	Max.	Unit		
	V	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	10			V		
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	12	0		V		
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	I _D = 250 μA		8		mV/°C		
V _{GS(th)} Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	V V I 050 ·· A	0.4	- 2.5		.,		
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	0.4		1	V		
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 5	- μΑ		
		$V_{DS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$			± 0.5			
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 12 V, V _{GS} = 0 V			1			
	366	$V_{DS} = 12 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			10			
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	10			Α		
		$V_{GS} = 4.5 \text{ V}, I_D = 5.2 \text{ A}$		0.023	0.028	Ω		
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 2.5 \text{ V}, I_D = 4.8 \text{ A}$		0.027	0.033			
		$V_{GS} = 1.8 \text{ V}, I_D = 2.5 \text{ A}$		0.035	0.042			
Forward Transconductance ^a	9 _{fs}	V _{DS} = 10 V, I _D = 5.2 A		23		S		
Dynamic ^b								
Input Capacitance	C _{iss}			455		pF		
Output Capacitance	C _{oss}	$V_{DS} = 6 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		190				
Reverse Transfer Capacitance	C _{rss}			150		1		
	Qg	V _{DS} = 6 V, V _{GS} = 8 V, I _D = 6.8 A		10.5	16	nC		
Total Gate Charge				6.2	9.5			
Gate-Source Charge	Q _{gs}	$V_{DS} = 6 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 6.8 \text{ A}$		0.8				
Gate-Drain Charge	Q _{gd}			1.6				
Gate Resistance	R _g	f = 1 MHz	0.8	4	8	Ω		
Turn-On Delay Time	t _{d(on)}			10	15			
Rise Time	t _r			12	20	ns		
Turn-Off Delay Time	t _{d(off)}	$V_{DD} = 6 \text{ V}, R_L = 1.1 \Omega$		25	40			
Fall Time	t _f	$I_D \cong 5.4 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$		12	20			
Turn-On Delay Time	t _{d(on)}			5	10			
Rise Time	t _r			10	15			
Turn-Off Delay Time	t _{d(off)}	$V_{DD} = 6 \text{ V}, R_L = 1.1 \Omega$		20	30			
Fall Time	t _f	$I_D \cong 5.4 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		10	15			
Drain-Source Body Diode Characteristic					1			
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C			4.5			
lse Diode Forward Current I _{SM}		<u> </u>			20	A		
Body Diode Voltage	V _{SD}	I _S = 5.4 A, V _{GS} = 0 V		0.8	1.2	V		
Body Diode Reverse Recovery Time	t _{rr}	0		25	50	ns		
Body Diode Reverse Recovery Charge	Q _{rr}			10	20	nC		
Reverse Recovery Fall Time	t _a	$I_F = 5.4 \text{ A}, \text{ dI/dt} = 100 \text{ A/}\mu\text{s}, T_J = 25 ^{\circ}\text{C}$		13		0		
Reverse Recovery Rise Time	t _b			12		ns		
Intee:	' b			12	1			

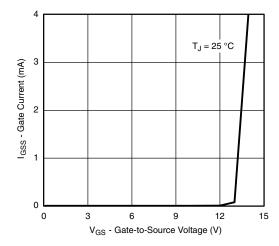
Notes:

- a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %
- b. Guaranteed by design, not subject to production testing.

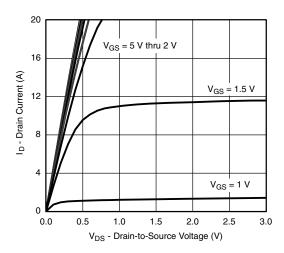
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



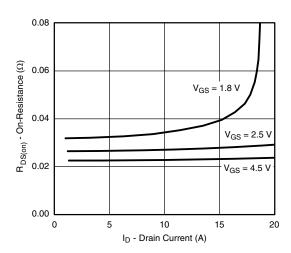
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



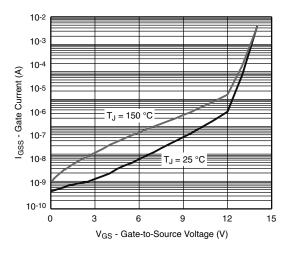
Gate Current vs. Gate-Source Voltage



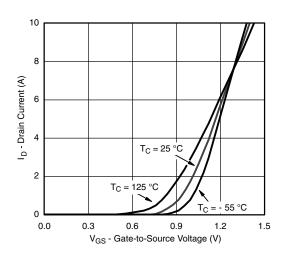
Output Characteristics



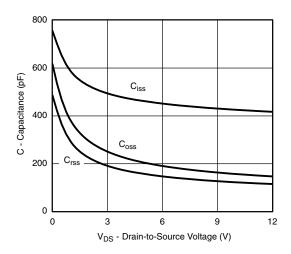
On-Resistance vs. Drain Current and Gate Voltage



Gate Current vs. Gate-Source Voltage

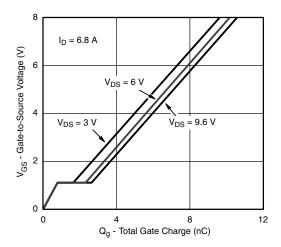


Transfer Characteristics

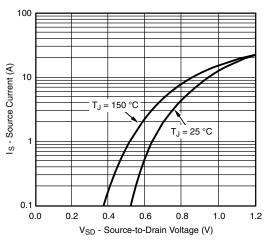


Capacitance

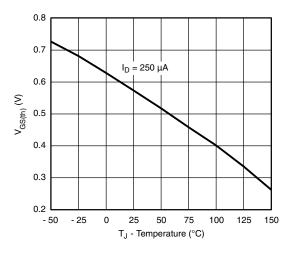
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



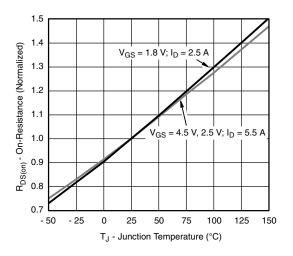
Gate Charge



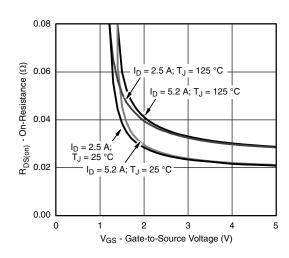
Source-Drain Diode Forward Voltage



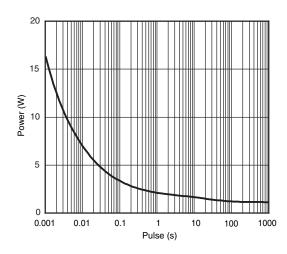
Threshold Voltage



On-Resistance vs. Junction Temperature



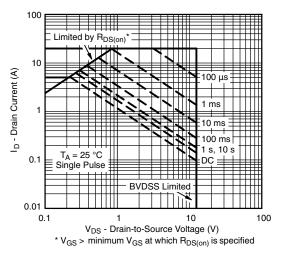
On-Resistance vs. Gate-to-Source Voltage



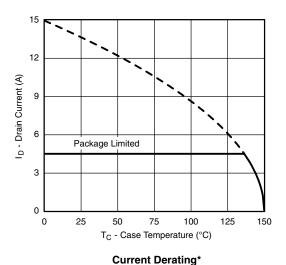
Single Pulse Power (Junction-to-Ambient)

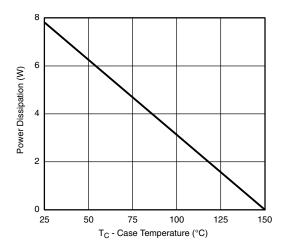


TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Safe Operating Area, Junction-to-Ambient



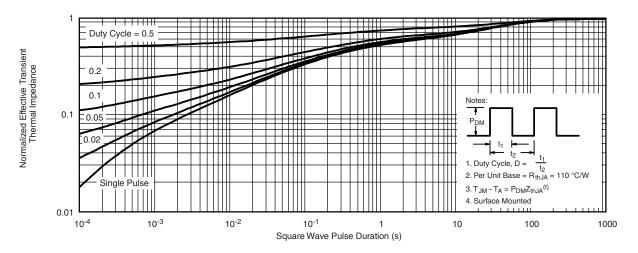


Power Derating

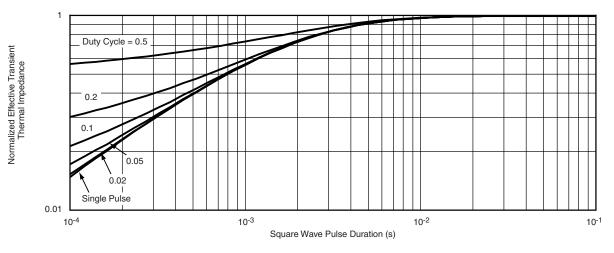
^{*} The power dissipation P_D is based on $T_{J(max.)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

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PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
 Package outline exclusive of mold flash and metal burr
 Package outline inclusive of plating

	SINGLE PAD						DUAL PAD					
DIM	MILLIMETERS			INCHES			MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032
A1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028
D2	0.135	0.235	0.335	0.005	0.009	0.013						
E	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041
E2	0.345	0.395	0.445	0.014	0.016	0.018						
E3	0.425	0.475	0.525	0.017	0.019	0.021						
е		0.65 BSC			0.026 BSC	;	0.65 BSC			0.026 BSC		
K		0.275 TYP			0.011 TYP		0.275 TYP		0.011 TYP			
K1		0.400 TYP		0.016 TYP			0.320 TYP			0.013 TYP		
K2		0.240 TYP		0.009 TYP			0.252 TYP			0.010 TYP		
К3		0.225 TYP		0.009 TYP					•	•		
K4		0.355 TYP		0.014 TYP								
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015
T							0.05	0.10	0.15	0.002	0.004	0.006

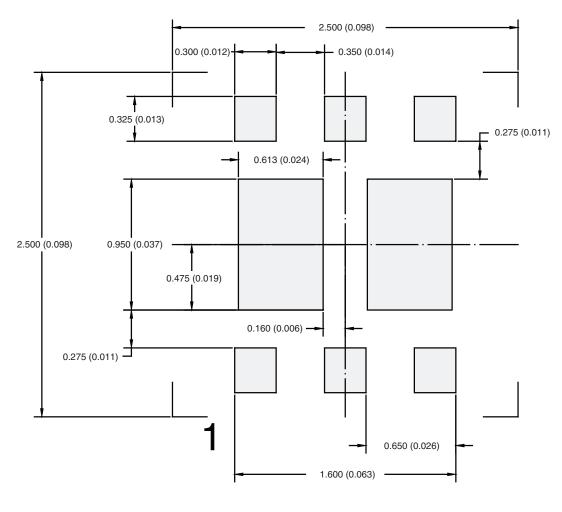
ECN: C-07431 - Rev. C, 06-Aug-07

DWG: 5934

06-Aug-07



RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Dual



Dimensions in mm (inches)

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Vishay

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Revision: 02-Oct-12 Document Number: 91000